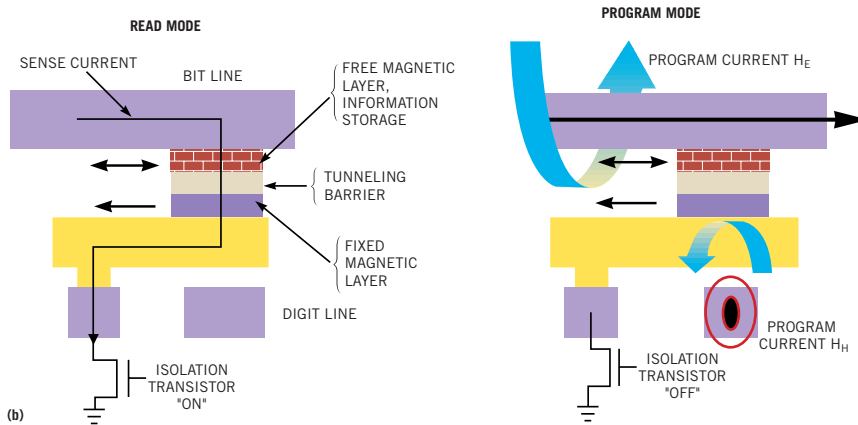


NOTES: I_x OR I_y ALONE DOESN'T SWITCH CELL.
 I_x AND I_y TOGETHER SWITCH CELL.

Figure 3



MRAMs rely on the magnetic field created by combined current of row- and column-decoding lines to, if necessary, flip the moment of the storage element (a, courtesy Nonvolatile Electronics). Some MRAM cells employ an isolation transistor to boost read performance (b, courtesy Motorola), whereas circular magnetic elements suppress cell-to-cell coupling effects at advanced process lithographies (c, courtesy Nonvolatile

